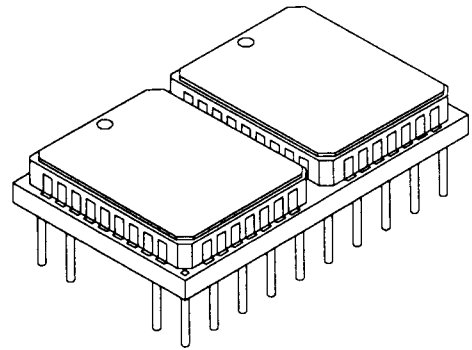


DESCRIPTION:

The DPE8X16A is a high-performance Electrically Erasable and Programmable Read Only Memory (EEPROM) module and may be organized as 8K X 16 or 16K X 8.

The module is built with two low-power CMOS 8K X 8 EEPROMs. The two chip enables are used for individual BW* selection. The DPE8X16A is ideally suited for those computer systems having 16-bit architectures.

The DPE8X16A contains a 32-BW page register to allow writing of up to 32 BWs simultaneously. During a write cycle, the address and 1 to 32 BWs of data are internally latched, freeing the address and data bus for other operations. Following the initiation of a write cycle, the module will automatically write the latched data using an internal control timer. The end of a write cycle can be detected by DATA Polling of the most significant data bit in each byte. Once the end of a write cycle has been detected, a new access for a read or write can begin.



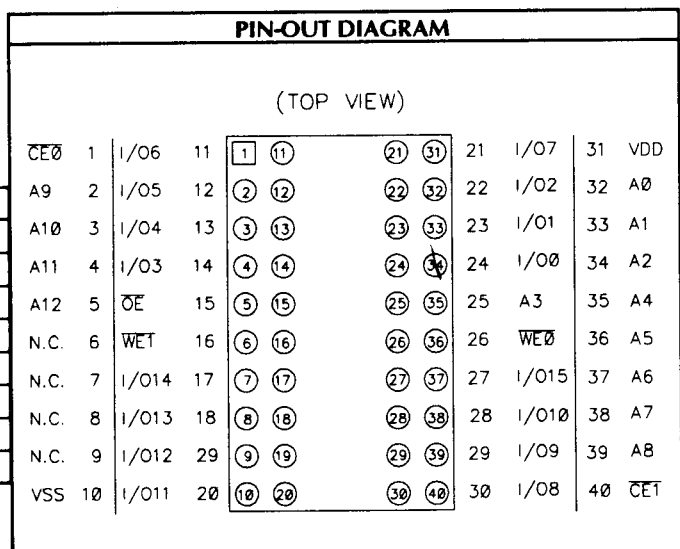
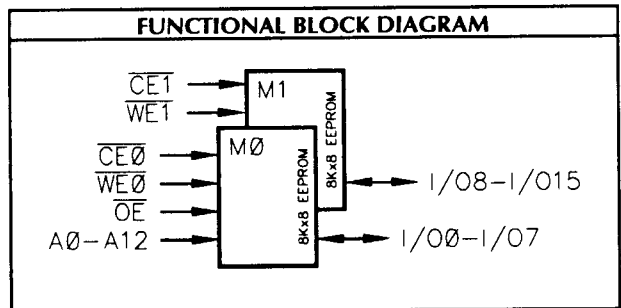
5

FEATURES:

- Fast Access Times: 55, 70, 90, 120, 150, 200, 250ns
- Automatic Page Write Operation
 - Internal Address and Data Latches
 - Internal Control Timer
- Fast Write Cycle Times
 - Page Write Cycle Time: 10ms maximum
 - 1 to 32 BW* Page Write Operation
- DATA Polling for END of Write Detection
- High Reliability CMOS Technology
 - Endurance: 10⁴ Cycles
 - Data Retention: 10 years
- Single +5V Power Supply, ±10% Tolerance
- CMOS and TTL Compatible Inputs and Outputs
- Available with All Semiconductor Components Compliant to MIL-STD-883; Class B
- 40-Pin PGA (Grid Array) Package

* Byte or Word (BW)

PIN NAMES	
A0 - A12	Address Inputs
I/O0 - I/O15	Data In/Out
$\overline{CE0}$, $\overline{CE1}$	Chip Enables
$\overline{WE0}$, $\overline{WE1}$	Write Enables
\overline{OE}	Output Enable
VDD	Power (+5V)
VSS	Ground
N.C.	No Connect



FOR FURTHER INFORMATION
SEE CHAPTER 10
FOR COMPLETE DATA SHEET